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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

505/503

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10036303	12/28/2001	257	5	2811	S. D. 2811

**APPLICANTS: Hawley Frank; Wang Daniel;

**CONTINUING DATA VERIFIED:

THIS APPLICATION IS A DIV OF 09/741,949 12/20/2000

** FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input checked="" type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		ACT-307DVA
Verified and Acknowledged Examiners's initials		
TITLE : Method for fabricating a MOS transistor having improved total radiation-induced leakage current		

U.S. DEPT. OF COMMERCE / PAT & TM-PTO-436L (Rev. 12-94)

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NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Assistant Examiner	Total Claims Print Claim for O.G.
ISSUE FEE		Primary Examiner	DRAWING
Amount Due	Date Paid		Sheets Drwg. Figs. Drwg. Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner
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